

### OptiMOS<sup>®</sup>-P Small-Signal-Transistor Feature

- P-Channel
- Enhancement mode
- Super Logic Level (2.5 V rated)
- 150°C operating temperature
- Avalanche rated
- dv/dt rated
- Pb-free lead plating; RoHS compliant
- Qualified according to AEC Q101

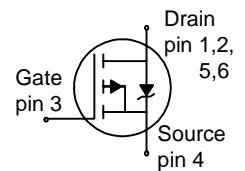
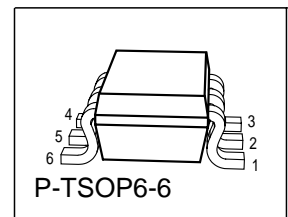


Type	Package	Tape and reel	Marking
BSL207SP	P-TSOP6-6	L6327:3000 pcs/r.	sPA

### Product Summary

$V_{DS}$	-20	V
$R_{DS(on)}$	41	mΩ
$I_D$	-6	A

P-TSOP6-6



### Maximum Ratings, at $T_j = 25\text{ °C}$ , unless otherwise specified

Parameter	Symbol	Value	Unit
Continuous drain current	$I_D$		A
$T_A=25\text{ °C}$		-6	
$T_A=70\text{ °C}$		-4.8	
Pulsed drain current	$I_D \text{ puls}$	-24	
$T_A=25\text{ °C}$			
Avalanche energy, single pulse	$E_{AS}$	44	mJ
$I_D=-6\text{ A}$ , $V_{DD}=-10\text{ V}$ , $R_{GS}=25\text{ }\Omega$			
Reverse diode dv/dt	dv/dt	-6	kV/ $\mu$ s
$I_S=-6\text{ A}$ , $V_{DS}=-16\text{ V}$ , $di/dt=200\text{ A}/\mu\text{s}$ , $T_{jmax}=150\text{ °C}$			
Gate source voltage	$V_{GS}$	$\pm 12$	V
Power dissipation	$P_{tot}$	2	W
$T_A=25\text{ °C}$			
Operating and storage temperature	$T_j, T_{stg}$	-55... +150	°C
IEC climatic category; DIN IEC 68-1		55/150/56	
ESD Class JESD22-A114-HBM		Class 1a	

**Thermal Characteristics**

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
<b>Characteristics</b>					
Thermal resistance, junction - soldering point	$R_{thJS}$	-	-	50	K/W
SMD version, device on PCB:	$R_{thJA}$				
@ min. footprint		-	-	230	
@ 6 cm <sup>2</sup> cooling area <sup>1)</sup>		-	-	62.5	

**Electrical Characteristics, at  $T_j = 25\text{ °C}$ , unless otherwise specified**

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
<b>Static Characteristics</b>					
Drain-source breakdown voltage $V_{GS}=0, I_D=-250\mu A$	$V_{(BR)DSS}$	-20	-	-	V
Gate threshold voltage, $V_{GS} = V_{DS}$ $I_D=-40\mu A$	$V_{GS(th)}$	-0.6	-0.9	-1.2	
Zero gate voltage drain current $V_{DS}=-20V, V_{GS}=0, T_j=25\text{ °C}$ $V_{DS}=-20V, V_{GS}=0, T_j=150\text{ °C}$	$I_{DSS}$	-	-0.1	-1	$\mu A$
Gate-source leakage current $V_{GS}=-12V, V_{DS}=0$	$I_{GSS}$	-	-10	-100	
Drain-source on-state resistance $V_{GS}=-2.5V, I_D=-4.9A$	$R_{DS(on)}$	-	43	65	m $\Omega$
Drain-source on-state resistance $V_{GS}=-4.5, I_D=-6A$	$R_{DS(on)}$	-	29	41	

<sup>1</sup>Device on 40mm\*40mm\*1.5mm epoxy PCB FR4 with 6cm<sup>2</sup> (one layer, 70  $\mu m$  thick) copper area for drain connection. PCB is vertical without blown air;  $t \leq 5$  sec.

Electrical Characteristics, at  $T_j = 25\text{ }^\circ\text{C}$ , unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

**Dynamic Characteristics**

Transconductance	$g_{fs}$	$V_{DS} \geq 2 \cdot I_D \cdot R_{DS(on)max}$ , $I_D = -4.8\text{A}$	7	14	-	S
Input capacitance	$C_{iss}$	$V_{GS} = 0$ , $V_{DS} = -15\text{V}$ , $f = 1\text{MHz}$	-	1007	-	pF
Output capacitance	$C_{oss}$		-	410	-	
Reverse transfer capacitance	$C_{rss}$		-	332	-	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = -10\text{V}$ , $V_{GS} = -4.5\text{V}$ , $I_D = -1\text{A}$ , $R_G = 6\Omega$	-	9	14	ns
Rise time	$t_r$		-	17	26	
Turn-off delay time	$t_{d(off)}$		-	42	63	
Fall time	$t_f$		-	53	76	

**Gate Charge Characteristics**

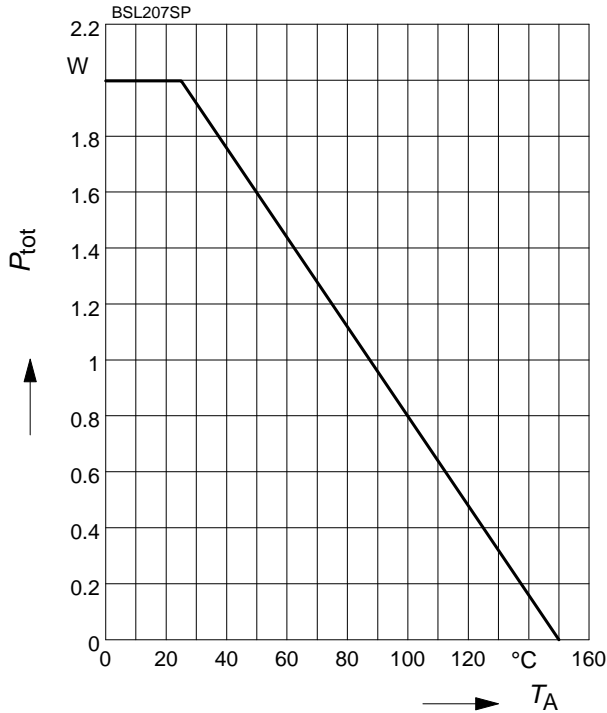
Gate to source charge	$Q_{gs}$	$V_{DD} = -10\text{V}$ , $I_D = -6\text{A}$	-	-1.7	-2.6	nC
Gate to drain charge	$Q_{gd}$		-	-7.1	-10.7	
Gate charge total	$Q_g$	$V_{DD} = -10\text{V}$ , $I_D = -6\text{A}$ , $V_{GS} = 0$ to $-4.5\text{V}$	-	-13.3	-20	
Gate plateau voltage	$V_{(plateau)}$	$V_{DD} = -10\text{V}$ , $I_D = -6\text{A}$	-	-1.6	-	V

**Reverse Diode**

Inverse diode continuous forward current	$I_S$	$T_A = 25\text{ }^\circ\text{C}$	-	-	-2.3	A
Inverse diode direct current, pulsed	$I_{SM}$		-	-	-24	
Inverse diode forward voltage	$V_{SD}$	$V_{GS} = 0$ , $ I_F  =  I_D $	-	-0.9	-1.3	V
Reverse recovery time	$t_{rr}$	$V_R = -10\text{V}$ , $ I_F  =  I_D $ , $di_F/dt = 100\text{A}/\mu\text{s}$	-	29	36	ns
Reverse recovery charge	$Q_{rr}$		-	12	15	nC

### 1 Power dissipation

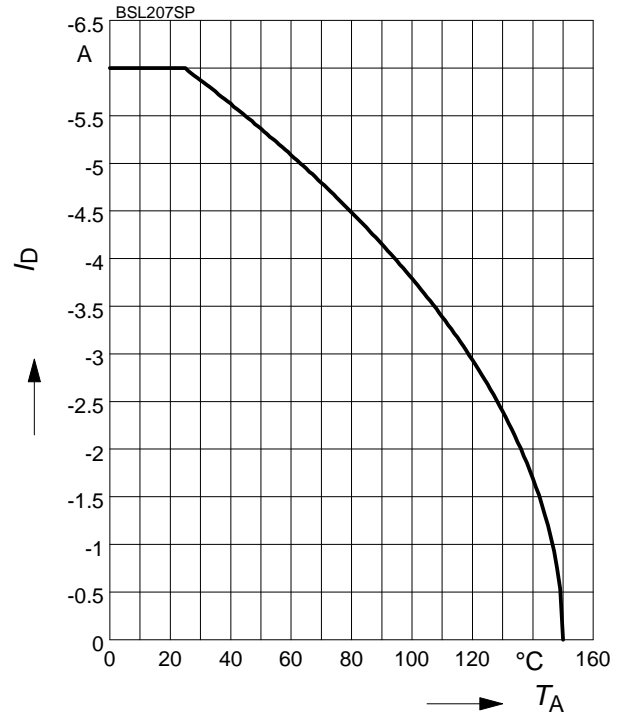
$$P_{tot} = f(T_A)$$



### 2 Drain current

$$I_D = f(T_A)$$

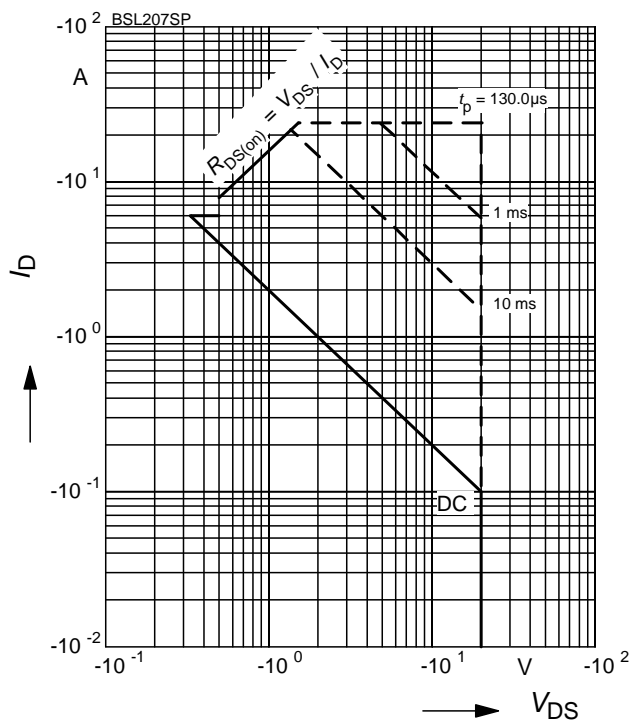
parameter:  $|V_{GS}| \geq 4.5 \text{ V}$



### 3 Safe operating area

$$I_D = f(V_{DS})$$

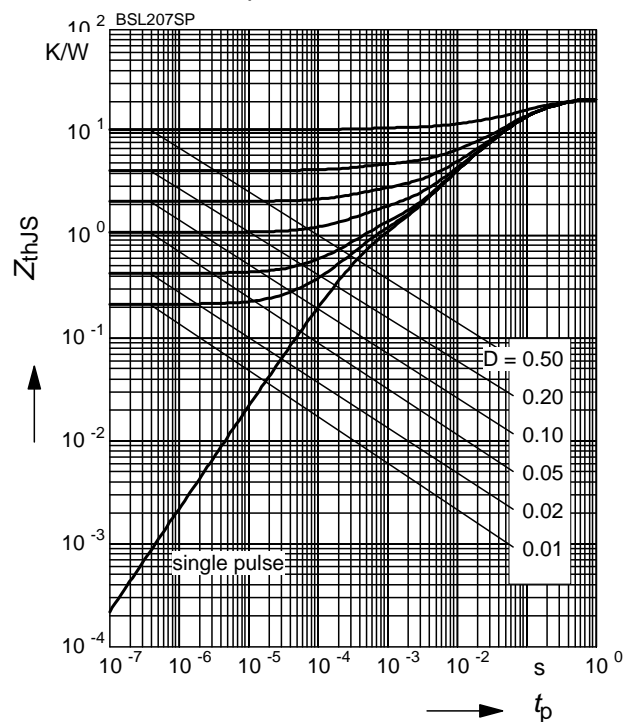
parameter:  $D = 0, T_A = 25 \text{ °C}$



### 4 Transient thermal impedance

$$Z_{thJS} = f(t_p)$$

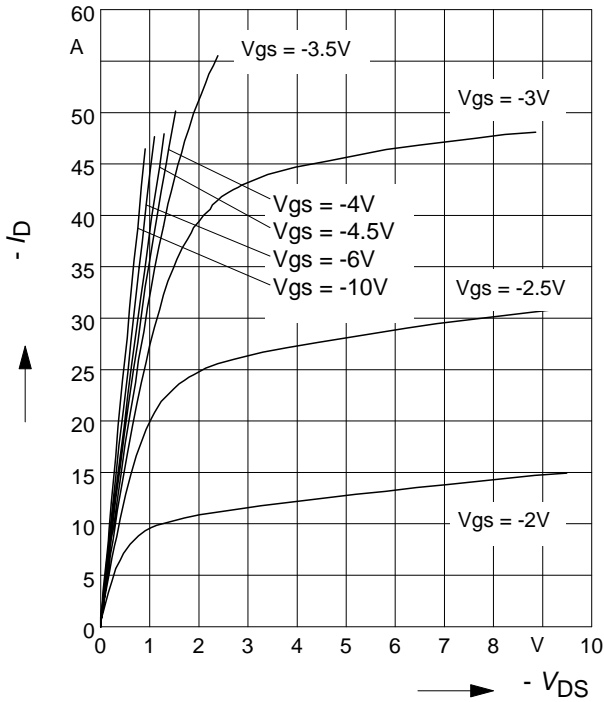
parameter:  $D = t_p/T$



**5 Typ. output characteristic**

$I_D = f(V_{DS}); T_j = 25^\circ\text{C}$

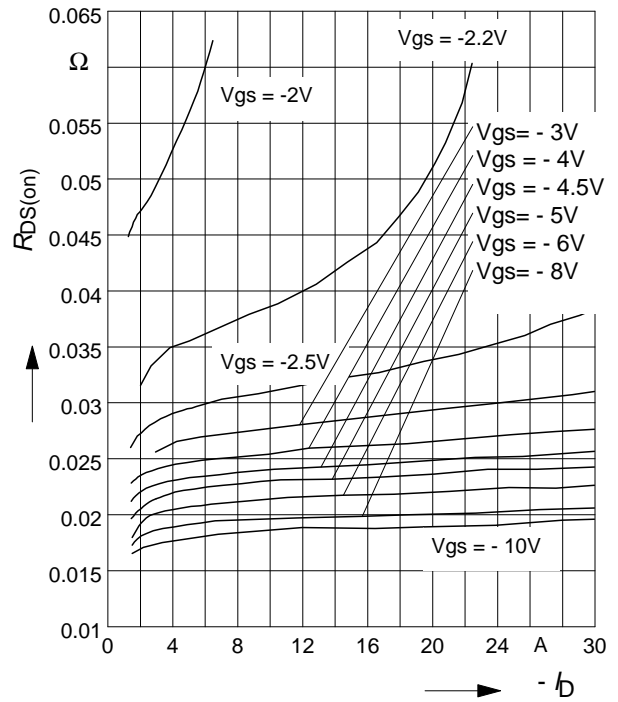
parameter:  $t_p = 80 \mu\text{s}$



**6 Typ. drain-source on resistance**

$R_{DS(on)} = f(I_D)$

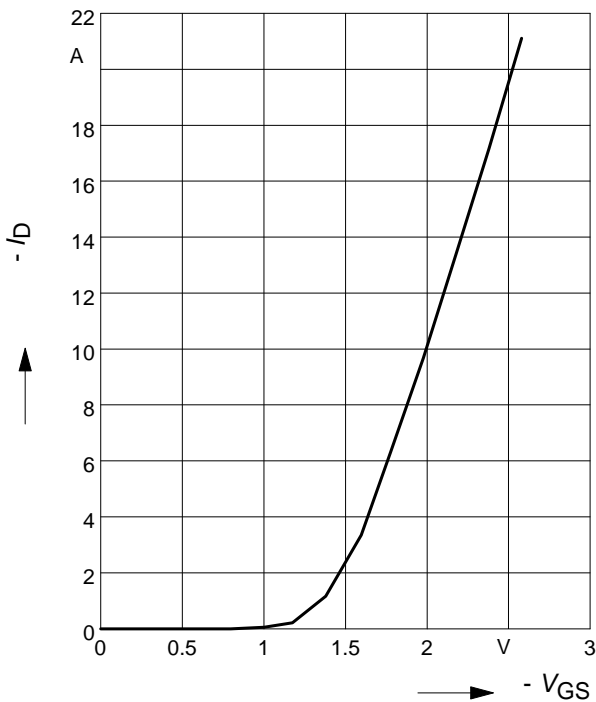
parameter:  $V_{GS}$



**7 Typ. transfer characteristics**

$I_D = f(V_{GS}); |V_{DS}| \geq 2 \times |I_D| \times R_{DS(on)max}$

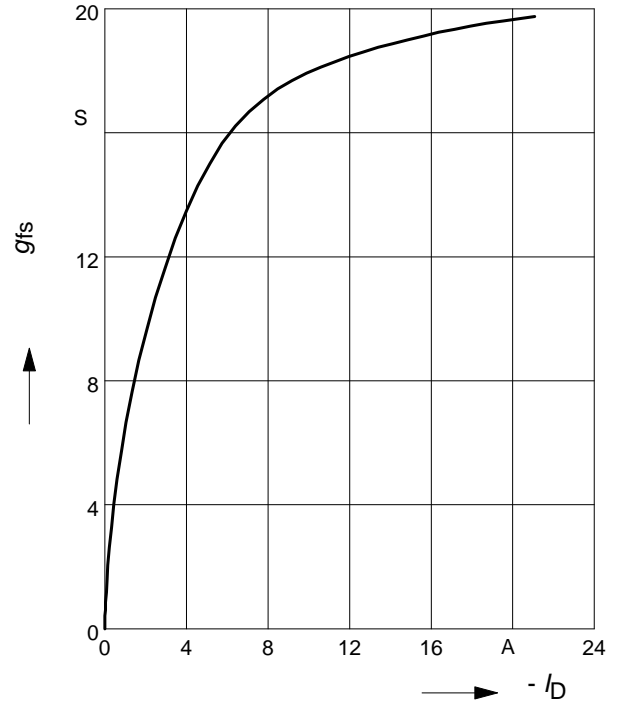
parameter:  $t_p = 80 \mu\text{s}$



**8 Typ. forward transconductance**

$g_{fs} = f(I_D); T_j = 25^\circ\text{C}$

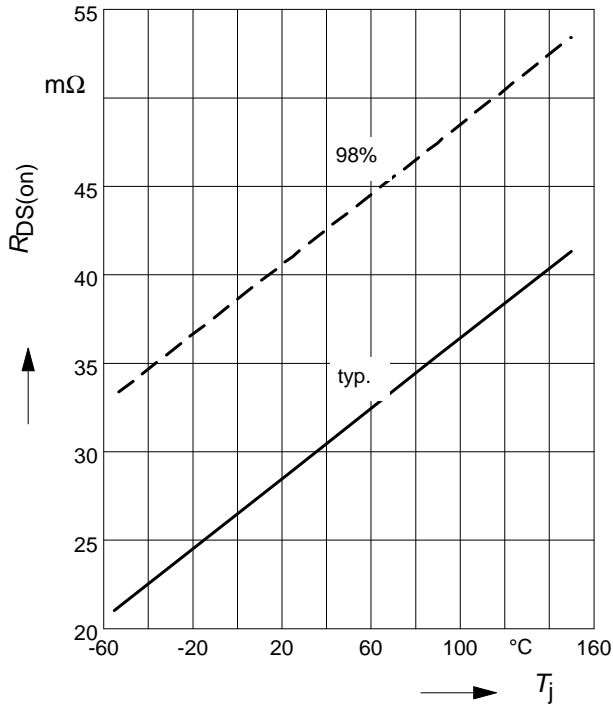
parameter:  $t_p = 80 \mu\text{s}$



**9 Drain-source on-resistance**

$$R_{DS(on)} = f(T_j)$$

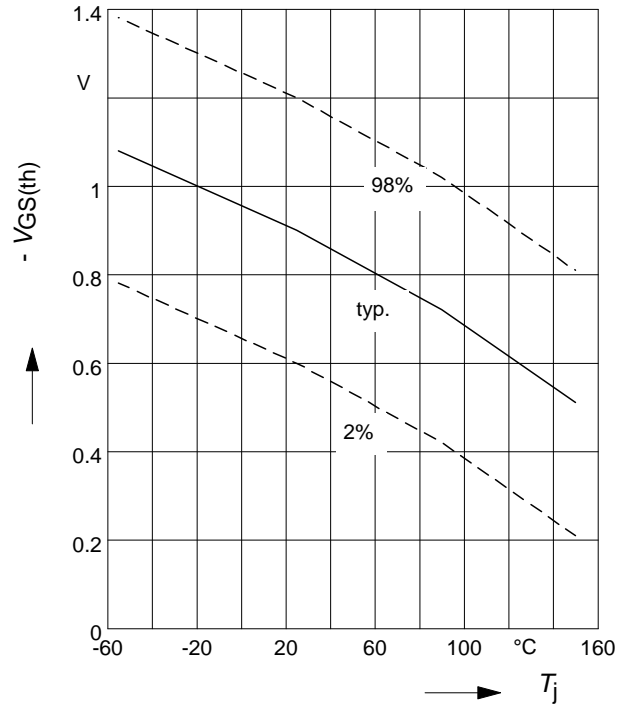
parameter:  $I_D = -6\text{ A}$ ,  $V_{GS} = -4.5\text{ V}$



**10 Gate threshold voltage**

$$V_{GS(th)} = f(T_j)$$

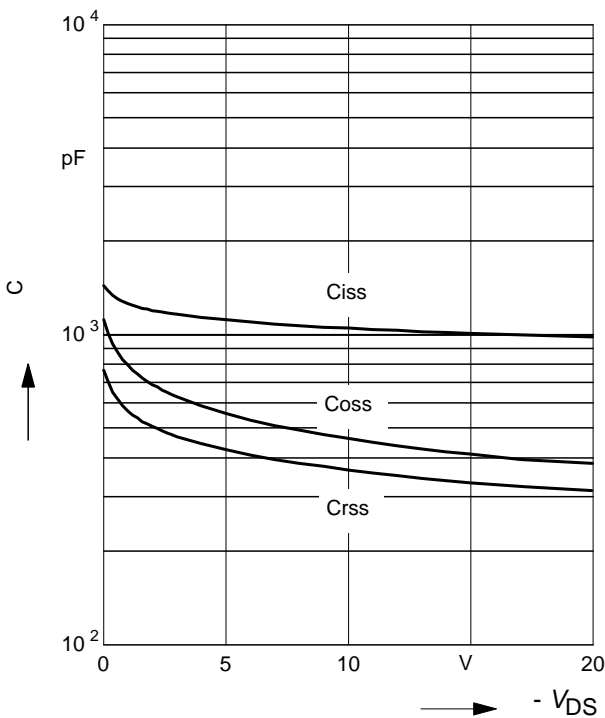
parameter:  $V_{GS} = V_{DS}$ ,  $I_D = -40\ \mu\text{A}$



**11 Typ. capacitances**

$$C = f(V_{DS})$$

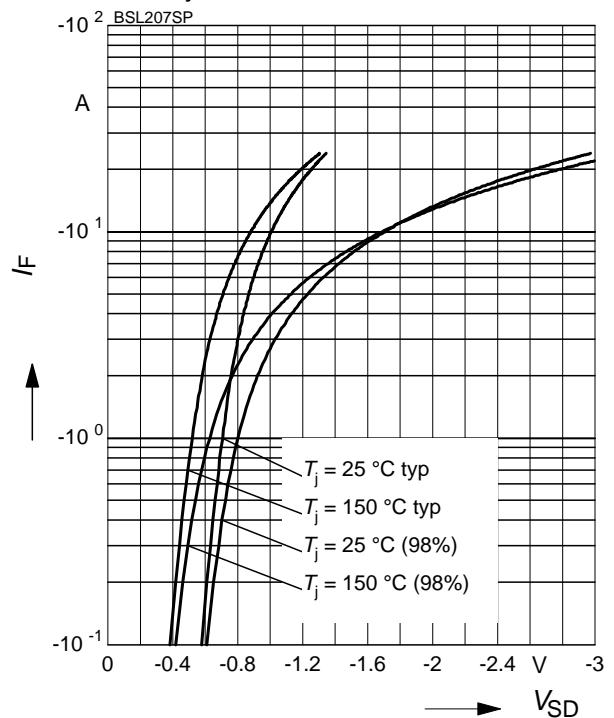
parameter:  $V_{GS}=0$ ,  $f=1\text{ MHz}$



**12 Forward character. of reverse diode**

$$I_F = f(V_{SD})$$

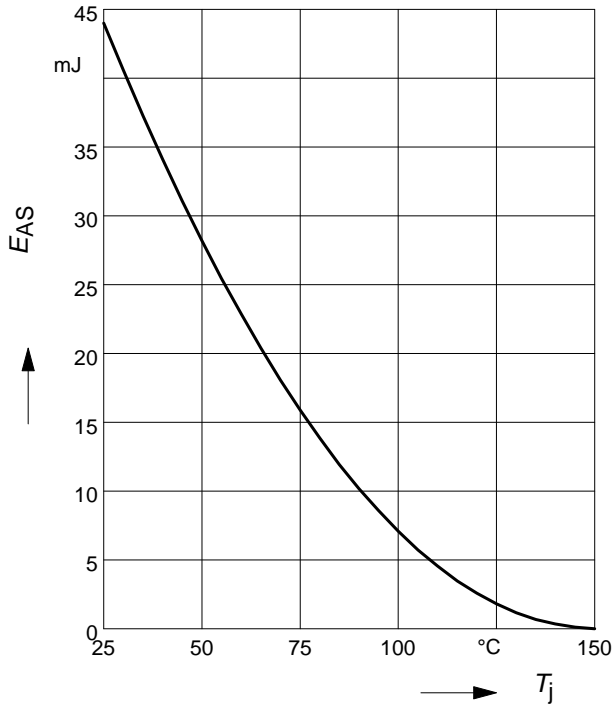
parameter:  $T_j$ ,  $t_p = 80\ \mu\text{s}$



**13 Typ. avalanche energy**

$E_{AS} = f(T_j)$ , par.:  $I_D = -6\text{ A}$

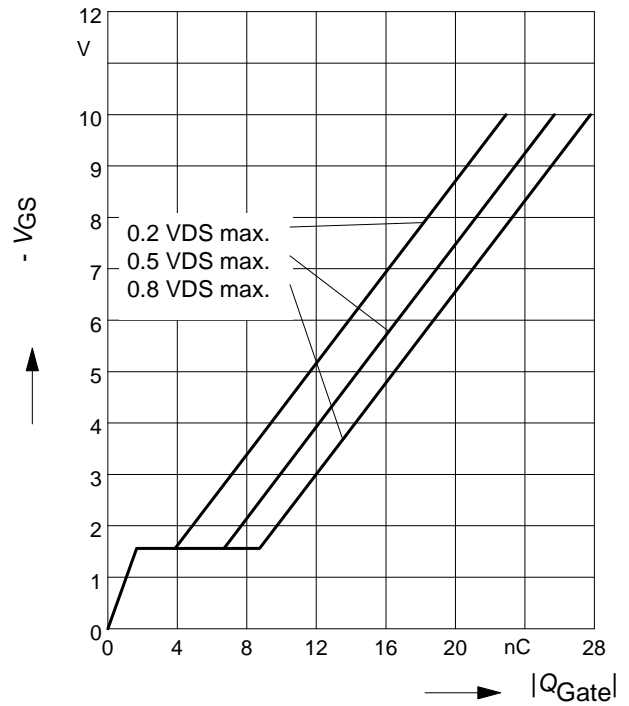
$V_{DD} = -10\text{ V}$ ,  $R_{GS} = 25\ \Omega$



**14 Typ. gate charge**

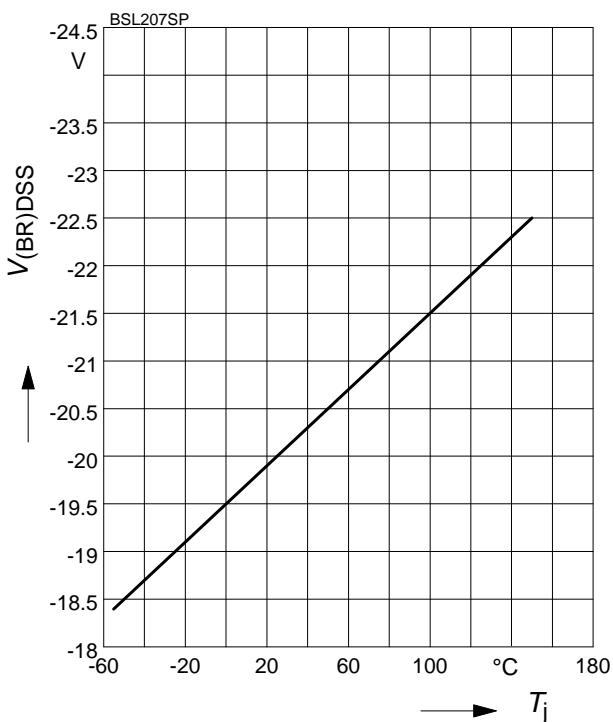
$|V_{GS}| = f(Q_{Gate})$

parameter:  $I_D = -6\text{ A}$  pulsed



**15 Drain-source breakdown voltage**

$V_{(BR)DSS} = f(T_j)$



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